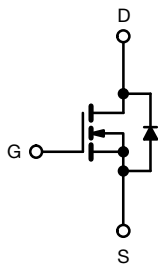
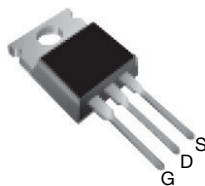


Power MOSFET

TO-220AB


N-Channel MOSFET

PRODUCT SUMMARY

V_{DS} (V)	500	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10\text{ V}$	0.21
Q_g max. (nC)	110	
Q_{gs} (nC)	33	
Q_{gd} (nC)	54	
Configuration	Single	

FEATURES

- Low gate charge Q_g results in simple drive requirement
- Improved gate, avalanche, and dynamic dV/dt ruggedness
- Fully characterized capacitance and avalanche voltage and current
- Low $R_{DS(on)}$
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS*
Available

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

APPLICATIONS

- Switch mode power supply (SMPS)
- Uninterruptible power supply
- High speed power switching
- Hard switched and high frequency circuits

ORDERING INFORMATION

Package	TO-220AB
Lead (Pb)-free	IRFB20N50KPbF
	SiHFB20N50K-E3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			V_{DS}	500	V
Gate-source voltage			V_{GS}	± 30	
Continuous drain current	V_{GS} at 10 V	$T_C = 25\text{ }^{\circ}\text{C}$	I_D	20	A
		$T_C = 100\text{ }^{\circ}\text{C}$		12	
Pulsed drain current ^a			I_{DM}	80	
Linear derating factor				2.2	W/ $^{\circ}\text{C}$
Single pulse avalanche energy ^b			E_{AS}	330	mJ
Repetitive avalanche current ^a			I_{AR}	20	A
Repetitive avalanche energy ^a			E_{AR}	28	mJ
Maximum power dissipation	$T_C = 25\text{ }^{\circ}\text{C}$		P_D	280	W
Peak diode recovery dV/dt ^c			dV/dt	10	V/ns
Operating junction and storage temperature range			T_J, T_{stg}	-55 to +150	$^{\circ}\text{C}$
Soldering recommendations (peak temperature) ^d	For 10 s			300	
Mounting torque	6-32 or M3 screw			10	N


Notes

- Repetitive rating; pulse width limited by maximum junction temperature
- Starting $T_J = 25\text{ }^\circ\text{C}$, $L = 1.6\text{ mH}$, $R_g = 25\text{ }\Omega$, $I_{AS} = 20\text{ A}$
- $I_{SD} \leq 20\text{ A}$, $dI/dt \leq 350\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 150\text{ }^\circ\text{C}$
- 1.6 mm from case

**THERMAL RESISTANCE RATINGS**

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	-	58	°C/W
Case-to-sink, flat, greased surface	R_{thCS}	0.50	-	
Maximum junction-to-case (drain)	R_{thJC}	-	0.45	

SPECIFICATIONS ($T_J = 25\text{ °C}$, unless otherwise noted)

= 25 °C,	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		500	-	-	V
V _{DS} temperature coefficient	ΔV _{DS} /T _J	Reference to 25 °C, I _D = 1 mA		-	0.61	-	V/°C
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		3.0	-	5.0	V
Gate-source leakage	I _{GSS}	V _{GS} = ± 30 V		-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	V _{DS} = 500 V, V _{GS} = 0 V		-	-	50	μA
		V _{DS} = 400 V, V _{GS} = 0 V, T _J = 125 °C		-	-	250	
Drain-source on-state resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 12 A ^b	-	0.21	0.25	Ω
Forward transconductance	g _{fs}	V _{DS} = 50 V, I _D = 12 A		11	-	-	S
Dynamic							
Input capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1.0 MHz, see fig. 5		-	2870	-	pF
Output capacitance	C _{Oss}			-	320	-	
Reverse transfer capacitance	C _{rss}			-	34	-	
Output capacitance	C _{Oss}	V _{GS} = 0 V	V _{DS} = 1.0 V, f = 1.0 MHz	-	3480	-	pF
Effective output capacitance	C _{Oss} eff.		V _{DS} = 400 V, f = 1.0 MHz	-	85	-	
Total gate charge	Q _g	V _{GS} = 10 V	V _{DS} = 0 V to 400 V	-	160	-	
Gate-source charge	Q _{gs}		I _D = 20 A, V _{DS} = 400 V see fig. 6 and 13 ^b	-	-	110	
Gate-drain charge	Q _{gd}		-	-	33		
Turn-on delay time	t _{d(on)}	V _{DD} = 250 V, I _D = 20 A R _g = 7.5 Ω, V _{GS} = 10 V, see fig. 10 ^b		-	22	-	ns
Rise time	t _r			-	74	-	
Turn-off delay time	t _{d(off)}			-	45	-	
Fall time	t _f			-	33	-	
Gate input resistance	R _g	f = 1 MHz, open drain		0.3	-	2.9	Ω
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I _S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	20	A
Pulsed diode forward current ^a	I _{SM}			-	-	80	
Body diode voltage	V _{SD}	T _J = 25 °C, I _S = 20 A, V _{GS} = 0 V ^b		-	-	1.5	V
Body diode reverse recovery time	t _{rr}	T _J = 25 °C, I _F = 20 A, dI/dt = 100 A/μs ^b		-	520	780	ns
Body diode reverse recovery charge	Q _{rr}			-	5.3	8.0	μC
Forward turn-on time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L _S and L _D)					

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature

b. Pulse width $\leq 400\text{ }\mu\text{s}$; duty cycle $\leq 2\%$



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

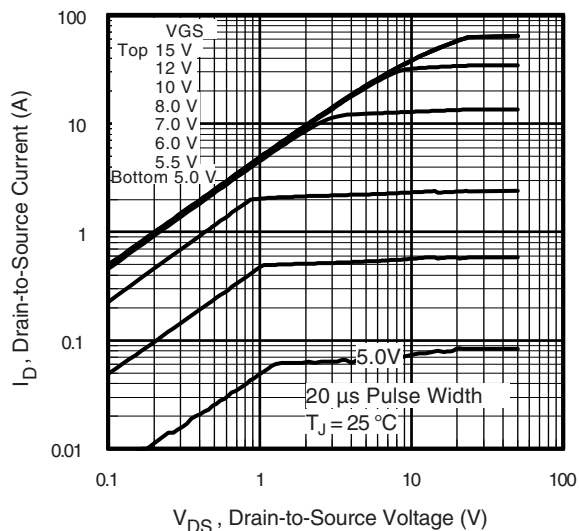


Fig. 1 - Typical Output Characteristics

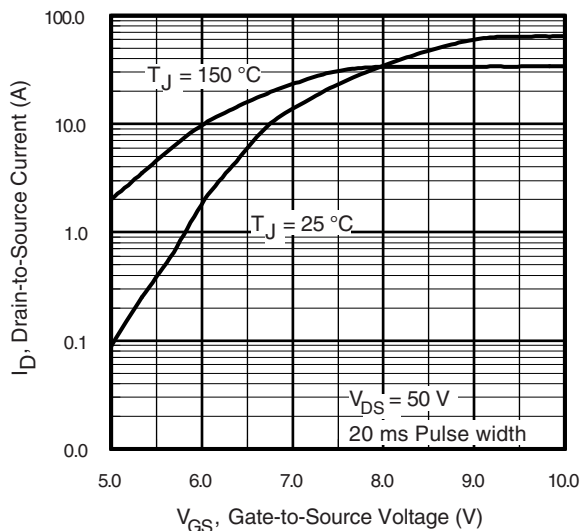


Fig. 3 - Typical Transfer Characteristics

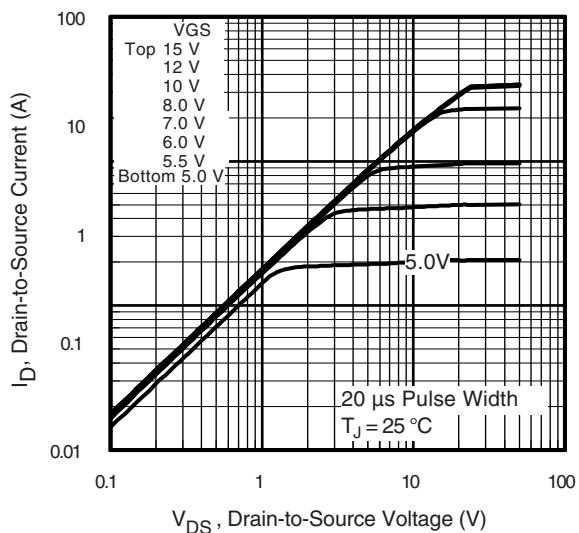


Fig. 2 - Typical Output Characteristics

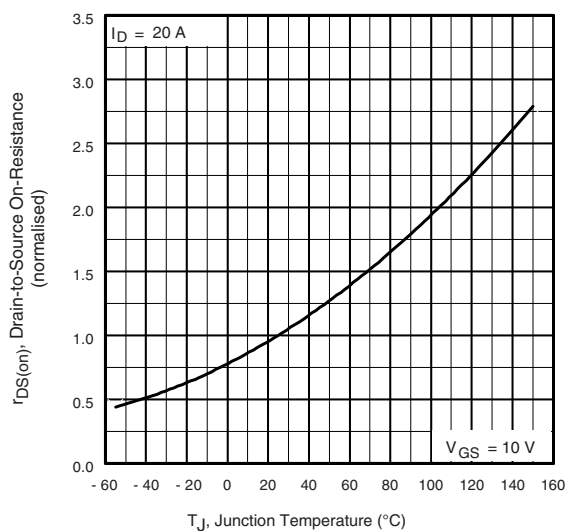
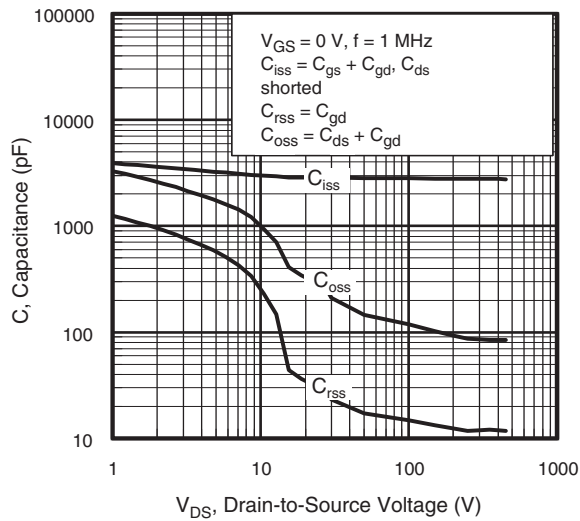
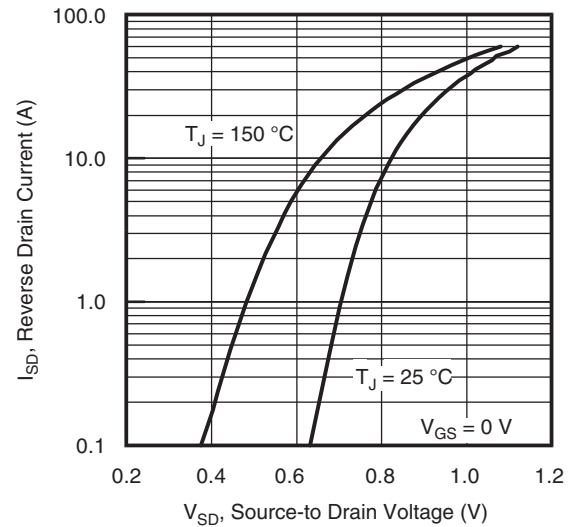
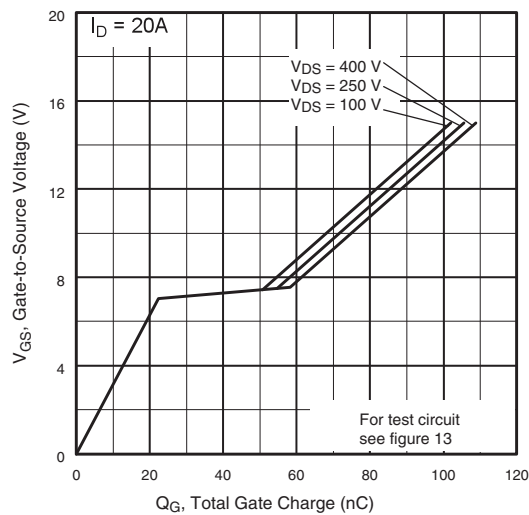
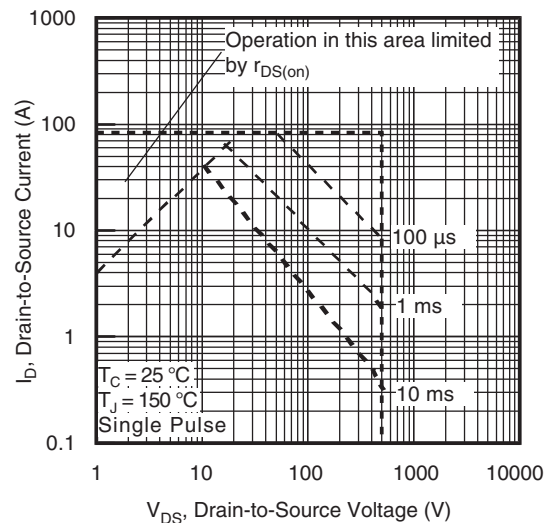
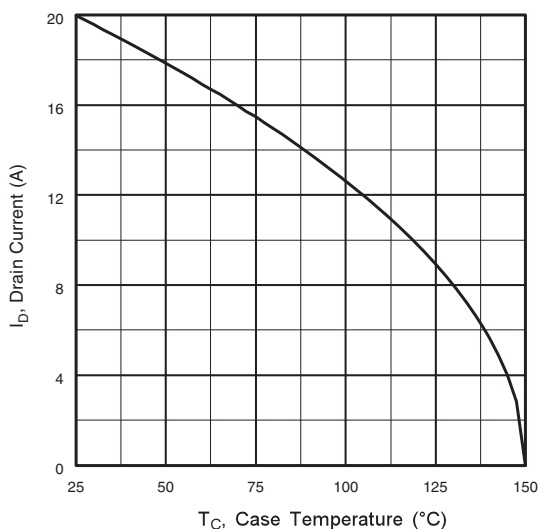
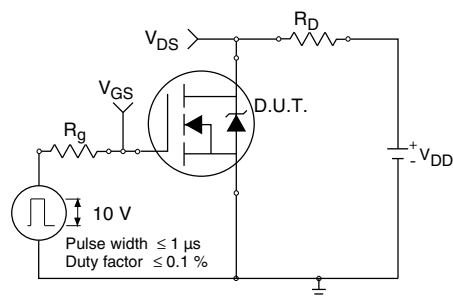
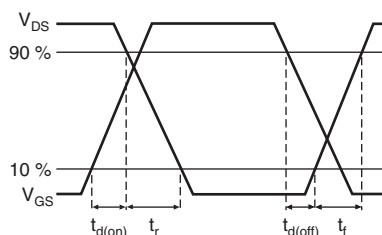
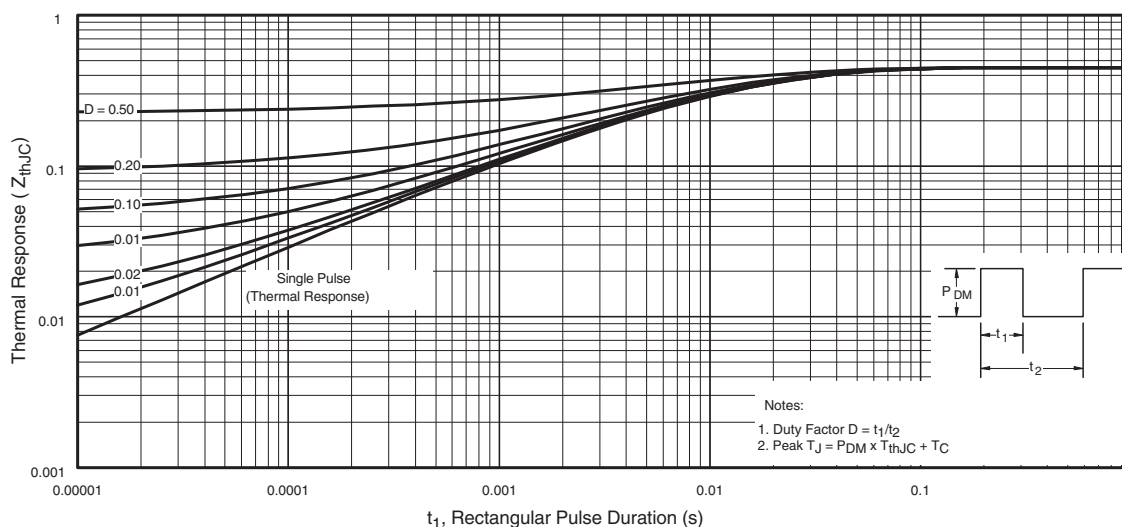
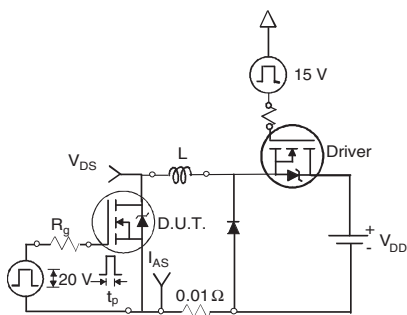
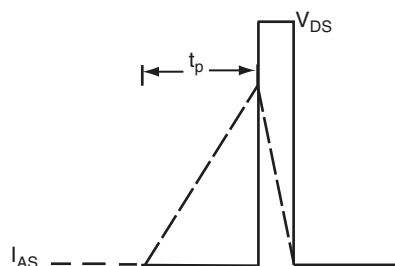
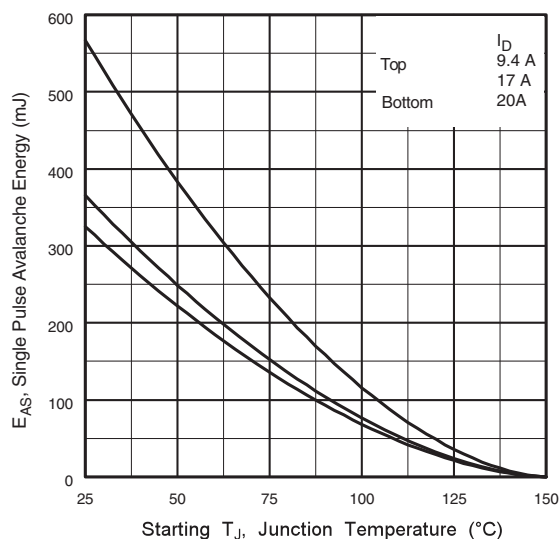
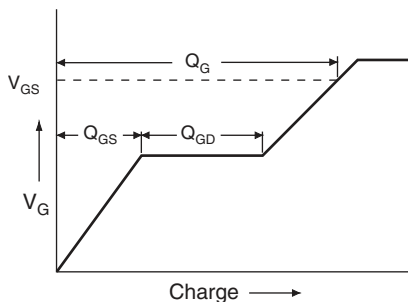
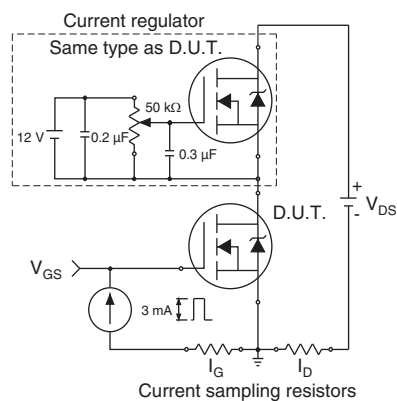


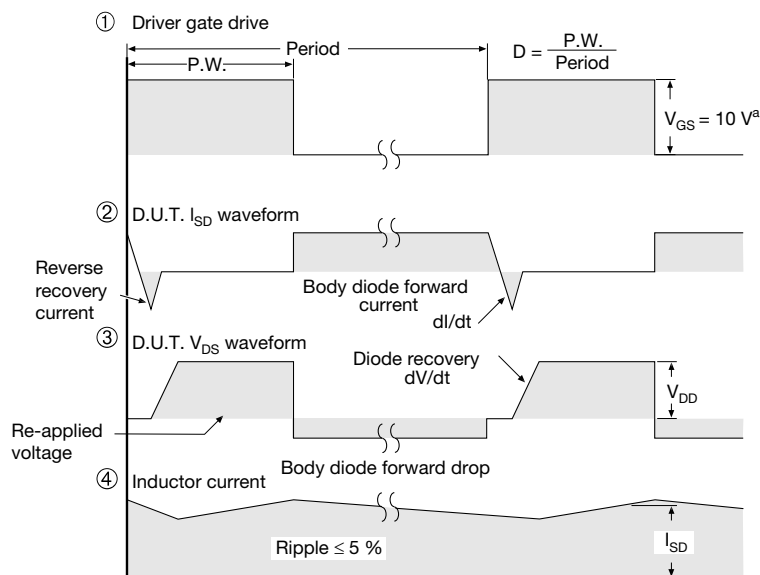
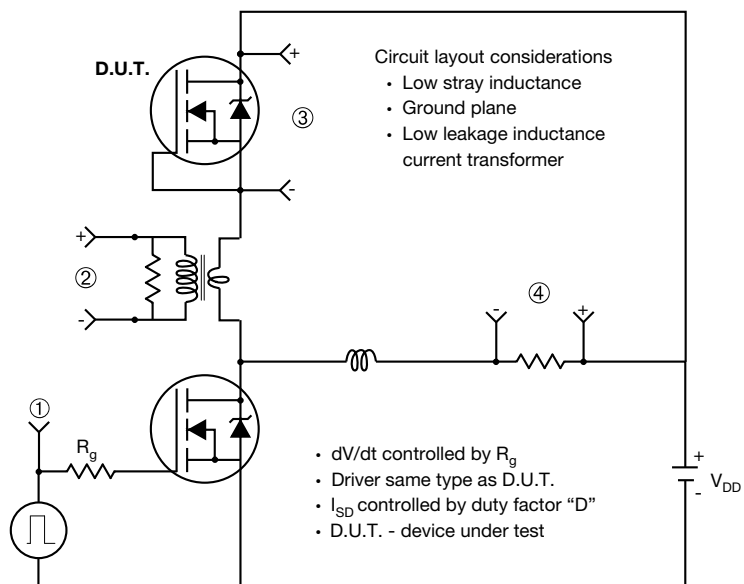
Fig. 4 - Normalized On-Resistance vs. Temperature


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

Fig. 7 - Typical Source-Drain Diode Forward Voltage

Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

Fig. 8 - Maximum Safe Operating Area


Fig. 9 - Maximum Drain Current vs. Case Temperature

Fig. 10a - Switching Time Test Circuit

Fig. 10b - Switching Time Waveforms

Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

Fig. 12a - Unclamped Inductive Test Circuit

Fig. 12b - Unclamped Inductive Waveforms


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

Fig. 13a - Basic Gate Charge Waveform

Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



Note

a. $V_{GS} = 5 \text{ V}$ for logic level devices

Fig. 14 - For N-Channel

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